

IN THE CLAIMS

Claims 9 and 13 had previously been canceled without prejudice.

Please add new claim 123.

Please enter the following claims:

*Subt E<sup>1</sup>*  
8. (Twice Amended) A gate electrode comprising:

a gate layer disposed above a substrate, said gate layer having a substantially level upper surface;

a conductive layer disposed over said gate layer, said conductive layer extending beyond edges of said gate layer;

thin first spacers disposed in contact with opposite sides of said gate layer and below said conductive layer; and

thick second spacers disposed in contact with said thin first spacers, said thick second spacers having a uniform width throughout its height.

*Subt E<sup>2</sup>*  
10. (Twice Amended) The gate electrode of claim 8 wherein said gate layer comprises polysilicon.

*D2*  
11. (Once Amended) The gate electrode of claim 10 wherein said conductive layer comprises polycide.

*D2*

~~E~~

12. (Twice Amended) The gate electrode of claim 8 wherein said thin first spacers comprise oxide.

---

*Subt E<sup>3</sup>*

*D3*

14. (Twice Amended) The gate electrode of claim 11 wherein said polycide comprises titanium salicide (TiSi<sub>2</sub>).

---

*Subt E<sup>4</sup>*

*D4*

123. (New) The gate electrode of claim 8 wherein said thick second spacers comprise nitride.

---